

Charge Storage and Reliability Characteristics of Nonvolatile Memory Capacitors with HfO₂/Al₂O₃-Based Charge Trapping Layers

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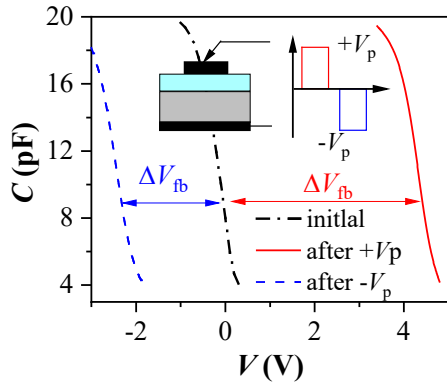


Figure S1. An illustration of the memory window definition. The memory window, ΔV is defined as the difference in the position of the measured C-V curves (measured flat band capacitance C_{fb}) after applying consecutively positive voltage pulse ($+V_p$), under which negative charges are injected from Si and trapped in CTL, and negative voltage pulse ($-V_p$), under which positive charges are injected and trapped in CTL. The inset shows the measurement procedure.